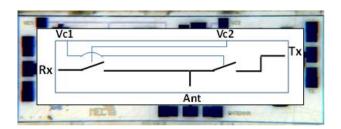
X-Band GaN HEMT TxRx Absorptive Switch





Product Description

MECGaNTRSX is a 0.25μm GaN HEMT Transmit/Receive Switch designed and tested by MEC for X-Band applications.

In the frequency range from 8 GHz to 11.5 GHz MECGaNTRSX provides less than 1.1 dB of small signal insertion loss, more than 28 dB of isolation, and less than 1.5 dB of insertion loss at 40 dBm of input power in transmit mode.

The Tx input port of the MECGaNTRSX is Absorptive.

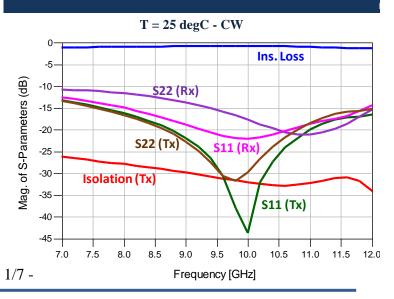
Main Features

- 0.25µm GaN HEMT Technology
- 8–11.5 GHz full performance Frequency Range
- Rx Small Signal Insertion Loss < 1.1 dB
- Tx Small Signal Insertion Loss < 1 dB
- Tx P1dB = 43 dBm
- Tx Insertion Loss @ Pin=40 dBm < 1.5 dB
- Input Power Handling = 46 dBm
- Isolation Tx-Rx > 28 dB
- Return Loss > 12 dB
- Tx absorptive port
- Rx reflective port
- Control Voltage: Vc = 0/-30V
- Chip Size: 3.00 x 1.00 x 0.10 mm³

Typical Applications

- Commercial and Military Radar
- Communications
- Test Instrumentation

Measured Data



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Main Characteristics - Rx Mode

Test Conditions: $T_{base_plate} = 25^{\circ}C$ (Vc1 = -30 V, Vc2 = -0 V) - CW

| Parameter | Min | Тур | Max | Unit |
|------------------------------------|-----|-----|------|------|
| Operating frequency | 8 | | 11.5 | GHz |
| Small Signal Insertion Loss | 0.8 | | 1.1 | dB |
| Isolation Tx-Rx | 20 | | 35 | dB |
| Input Return Loss (Ant) | 15 | | 22 | dB |
| Output Return Loss (Rx) | 12 | | 21 | dB |
| Return Loss @ Tx port (Absorptive) | 5 | | 15 | dB |
| Gate Control Voltage Vc1 | -30 | | -25 | V |
| Gate Control Voltage Vc2 | 0 | | 1 | V |
| Control Current | | | 0.5 | mA |

Main Characteristics - Tx Mode

Test Conditions: $T_{base_plate} = 25$ °C (Vc1 = 0 V, Vc2 = -30 V) - Pulsed

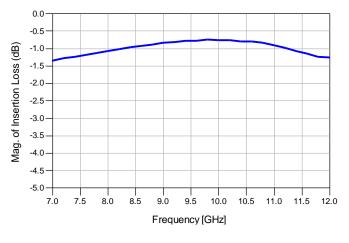
| Parameter | Min | Тур | Max | Unit |
|------------------------------------|-----|-----|------|------|
| Operating frequency | 8 | | 11.5 | GHz |
| Small Signal Insertion Loss | 0.8 | | 1 | dB |
| Isolation Tx-Rx | 28 | | 33 | dB |
| Input Return Loss (Tx) | 17 | | 40 | dB |
| Output Return Loss (Ant) | 17 | | 32 | dB |
| Return Loss @ Rx port (Reflective) | | 4 | | dB |
| Pin - 1 dB | | 43 | | dBm |
| Insertion Loss @ Pin=40 dBm | | 1.3 | | dB |
| Input Power Handling | | 46 | | dBm |
| Gate Control Voltage Vc1 | 0 | | 1 | V |
| Gate Control Voltage Vc2 | -30 | | -25 | V |
| Control Current | | | 0.5 | mA |

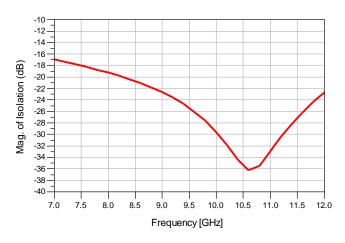


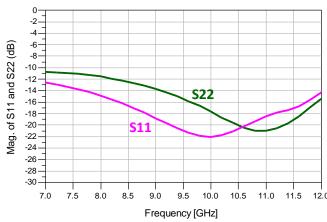


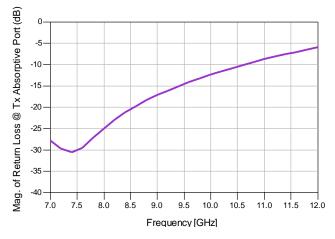
Receive Mode: Insertion Loss, Isolation and Return Loss

Test Conditions: $T_{base_plate} = 25^{\circ}C$, Vc1 = -30 V, Vc2 = 0 V - CW







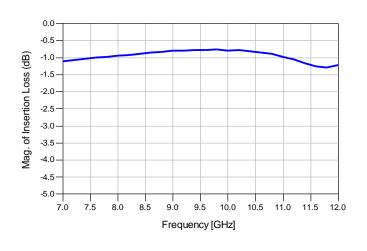


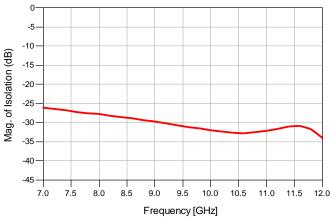
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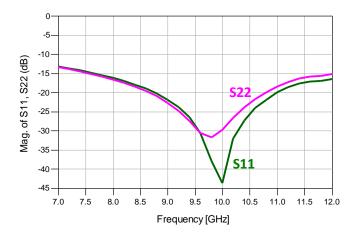


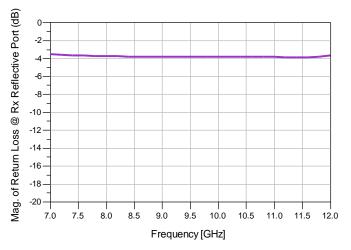
Transmit Mode: Insertion Loss, Isolation and Return Loss

Test Conditions: $T_{base\ plate} = 25^{\circ}C$, $Vc1 = 0\ V$, $Vc2 = -30\ V$ - CW







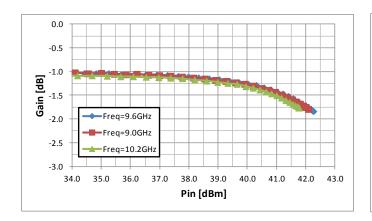


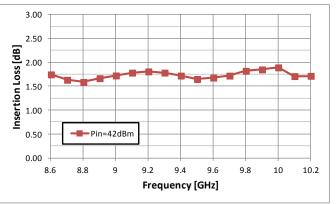
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Transmit Mode Nonlinear Measurement: Insertion Loss

Test Conditions: $T_{base_plate} = 25^{\circ}C$, Vc1 = 0 V, Vc2 = -30 V - Pulsed



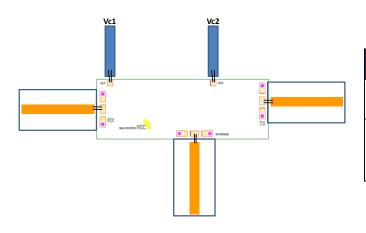


| Function Table | | | | |
|----------------|----------|-------|-------|--|
| RF path | State | Vc1 | Vc2 | |
| Antenna to Rx | Receive | -30 V | 0 V | |
| Tx to Antenna | Transmit | 0 V | -30 V | |

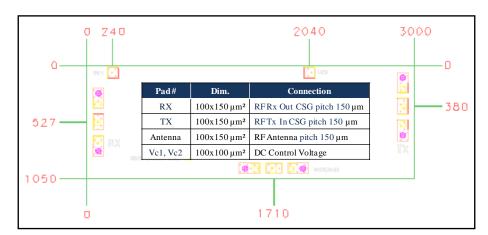
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Bond Pad Configuration & Assembly Recommendations



| Bond Pad# | Connection | External Components |
|-----------------------|-----------------------------------|---|
| Rx, Tx and Antenna | 2 Bonding Wires L_bond = 0.3nH | |
| Vc1, Vc2 | L_bond ≤ 1 nH | No external components required (Internal Series Resistance: Rs=4kΩ) |



Eutectic Die bond using AuSn (80/20) solder is recommended.

The backside of the die is the Source (ground) contact.

Thermosonic ball or wedge bonding are the preferred connection methods.

Gold wire must be used for connections.

Bias Procedure

Bias-Up

- 1. Vc1 and Vc2 sets to Control Voltage.
- 2. Apply RF signal.

Bias-Down

- 1. Turn off RF signal.
- 2. Turn off Vc1, Vc2.

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Notice

The furbished information is believed to be reliable. However, performances and specifications contained herein are based on preliminary characterizations and then susceptible to possible variations. On the basis of customer requirements the product can be tested and characterized in specific operating conditions and, if needed, tuned to meet custom specifications.

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